

SILICON BRIDGE RECTIFIER

REVERSE VOLTAGE : 50 --- 1000 V CURRENT: 1.5A

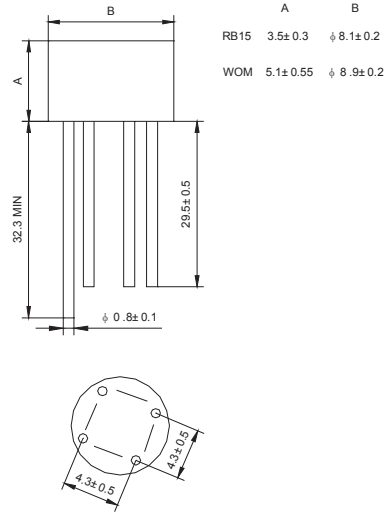
FEATURES

- Rating to 1000V PRV
- Surge overload rating to 50 Amperes peak
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- Glass passivated chip junctions

MECHANICAL DATA

- Mounting Position: Any

WOM



Dimensions in millimeters

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

		RB151	RB152	RB153	RB154	RB155	RB156	RB157	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum average forward Output current @ $T_A=55^\circ\text{C}$	$I_{F(AV)}$	1.5							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	I_{FSM}	50.0							A
Maximum instantaneous forward voltage @ 1.5 A	V_F	1.0							V
Maximum reverse current @ $T_A=25^\circ\text{C}$ at rated DC blocking voltage @ $T_A=100^\circ\text{C}$	I_R	10.0 0.5							μA mA
Operating junction temperature range	T_J	- 55 ---- + 125							°C
Storage temperature range	T_{STG}	- 55 ---- + 150							°C

RATINGS AND CHARACTERISTIC CURVES

FIG.1 – DERATING CUTPUT RECTIFIED CURRENT

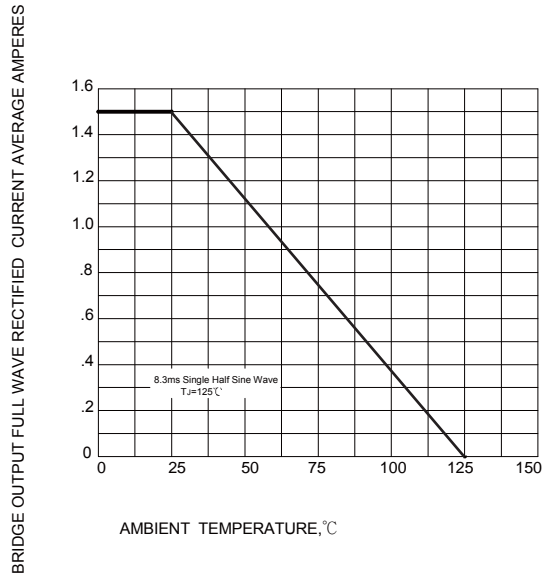


FIG.2 – MAXIMUM FORWARD SURGE CURRENT

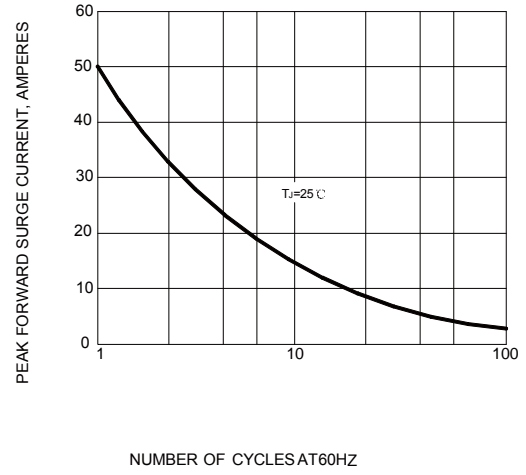


FIG.3 – TYPICAL FORWARD CHARACTERISTIC

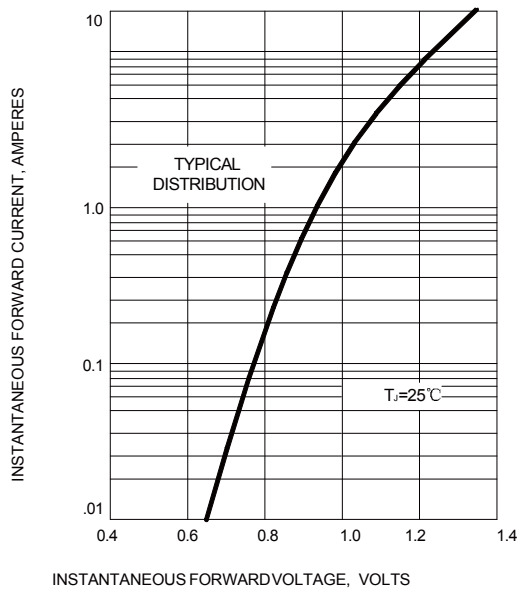


FIG.4 – TYPICAL REVERSE CHARACTERISTIC

